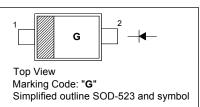
# SCHOTTKY BARRIER DIODE

## **Features**

- · Low power rectified
- · Silicon epitaxial type
- High reliability

#### **PINNING**

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings (T<sub>a</sub> = 25 °C)

Parameter	Symbol	Value	Unit
Reverse Voltage	V <sub>R</sub>	30	V
Forward Current	I <sub>F</sub>	0.2	А
Repetitive Peak Forward Current	I <sub>FRM</sub>	0.5	Α
Non-Repetitive Peak Forward Current (10 ms)	I <sub>FSM</sub>	2	Α
Power Dissipation	P <sub>D</sub>	150	mW
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature Range	T <sub>s</sub>	- 55 to + 150	°C

# Characteristics at $T_a = 25$ °C

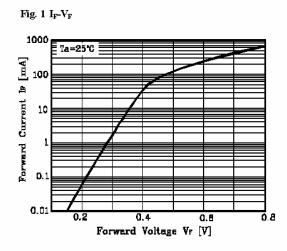
Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 10 \text{ mA}$ at $I_F = 30 \text{ mA}$	$V_{F}$	0.4 0.5	V
Reverse Current at V <sub>R</sub> = 30 V	I <sub>R</sub>	1	μΑ
Total Capacitance at V <sub>R</sub> = 1 V, f = 1 MHz	Ст	10	pF
Reverse Recovery Time at $I_F = I_R = 10$ mA, $I_{RR} = 1$ mA, $R_L = 100$ $\Omega$	t <sub>rr</sub>	5	ns

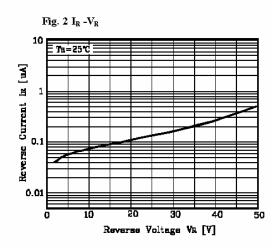




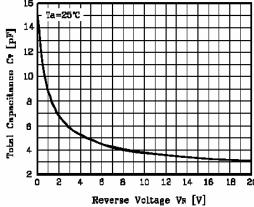




















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## **PACKAGE OUTLINE**

## Plastic surface mounted package; 2 leads

**SOD-523** 

